	S7	S6	SS	S4	\$2	SI	# Z
		<u></u>	σ	4	~~~~~		# Ref
327	49623	52626	18	~	165	75	Hits
S7 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)	S6 and @ad<"20040114"	(check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET MOSFET BJT transistor)	S2 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	S1 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	(324/602,600.ccls.) and @ad<"20040114"	(324/609.ccls.) and @ad<"20040114"	Search Query
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	DBs
O _R	Q _R	Q.	O _R	O _R	O _R	O _R	Default Operator
Q _N	Q 2	Q.	9	Q.	O _N	O _N	Plurals
2005/05/12 15:53	2005/05/12 14:21	2005/05/12 13:00	2005/05/12 15:51	2005/05/13 13:26	2005/05/13 13:21	2005/05/16 06:57	Time Stamp

S15	S14	S13	S12	S11	S10	65
27	504	N	ω	11	18	206
\$14 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET MOSFET BJT transistor)	(455/127.1.ccls.) and @ad<"20040114"	S9 and battery near3 (charg\$3 near (level state status capacity))	S8 and battery near3 (charg\$3 near (level state status capacity))	S9 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1am) near3 (capacitor sampling)	S8 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1am) near3 (capacitor sampling)	S7 and ((capacitor sampling) near2 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
Q _R	O _R	O _R	O _R	OR	O _R	O _R
Q.	N N	8	S _O	N _O	O _N	Q.
2005/05/12 13:00	2005/05/12 12:59	2005/05/12 14:18	2005/05/12 15:00	2005/05/12 14:39	2005/05/13 13:24	2005/05/12 14:22

S22 1	521 1	S20	S19	S18	S17	\$16
10883	11544	P	И	37	878	911
S21 and @ad<"20040114"	battery near3 (charg\$3 near (level state status capacity))	S19 and battery	S18 and (charg\$3 near2 (level state status capacity))	S17 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1amp (op adj amp)) near3 (capacitor sampling)	S16 and @ad<"20040114"	((capacitor sampling) near2 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
OR	O _R	O _R	Q _R	Q _R	O _R	O _R
ON	Q.	Q	O _N	Q.	Q	Q
2005/05/12 14:38	2005/05/12 14:37	2005/05/12 14:25	2005/05/12 14:26	2005/05/12 15:08	2005/05/12 14:38	2005/05/12 14:21

S29	S28	S27	S26	S25	S24	S23
		7				
		(.)	5.1		1025	
14	2	33	79	ω (0.40		14
(("5769873") or ("5627740") or ("5831562") or ("5963156") or ("6285220") or ("6426657") or ("6529049")).PN.		S26 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1amp (op adj amp))	S24 and (capacitor sampling) same (sampl\$3 near2 voltage)	S24 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)	S7 and battery near3 (charg\$3 near (level state status capacity))	S22 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
Ç	Q.	O _R	Я Я	O _R	OR	Q _R
C T	ON	Q	O _N	ON	O	O _N
2005/05/12 15:48	2005/05/12 15:10	2005/05/12 15:40	2005/05/12 15:08	2005/05/12 15:07	2005/05/12 15:01	2005/05/12 15:02

S36	S35	S34	S33	S32	S31	S30
4	126	77	1599	699	p.a.	w
S34 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	S33 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1am) near3 (capacitor sampling)	S32 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1am) near3 (capacitor sampling)	(327/91-96.ccls.) and @ad<"20040114"	(327/9,55,56,337.ccls.) and @ad<"20040114"	S29 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)	S29 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
OR	O _R	O _R	OR	OR	OR	O _R
Q	O _Z	Q	9	O _N	9	Q
2005/05/13 13:27	2005/05/13 13:25	2005/05/13 13:26	2005/05/13 13:23	2005/05/13 14:05	2005/05/13 15:23	2005/05/12 15:54

EPO; JPO; DERWENT; IBM_TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB

2005/05/13 14:14	Q.	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	545 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	169	S50
2005/05/13 14:47	Q.	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	12 \$44 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)		S49
2005/05/13 14:45	Q	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11 S43 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	ı.	S48
2005/05/13 14:13	Q.	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	52 S42 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	252	S47
2005/05/13 14:05	Q.	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	80 (323/282,353.ccls.) and @ad<"20040114"	1380	S46
2005/05/13 14:03	Q.	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	38 (363/76,78,89.ccls.) and @ad<"20040114"	738	S45
2005/05/13 14:03	Q.	OR.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	20 (341/172.ccls.) and @ad<"20040114"	520	S44

USPAT; EPO; JPO; DERWENT; IBM_TDB
IBM_TDB US-PGPUB; OR
US-PGPUB; OR USPAT; EPO; JPO; DERWENT;
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB
US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB
S47 and (switch\$3 (charg\$3 adj transfer\$5)) same (amplifier op\$1am) same US-PGPUB; OR (capacitor sampling) EPO; JPO; DERWENT; IBM_TDB

S64	S63	S62	S61	S60	S59	330
	₩	¥2	<u>~</u>		-	
–	0	0	0	ω	H	
\$32 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	\$45 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	\$44 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	\$43 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	\$42 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	S58 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)	
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	USPAT; EPO; JPO; DERWENT; IBM_TDB				
O _R	Q _R	OR.	P	R	₽ P	,
Q	Q	Q	Q	Q	O _Z	
2005/05/13 15:49	2005/05/13 15:38	2005/05/13 15:37	2005/05/13 15:37	2005/05/13 15:45	2005/05/13 15:52	

(check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way
\$57 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)
\$56 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)
\$55 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)
\$54 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)
\$33 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)

578	577	576	S75	574	573	572
133	6	78	318	344	6	н
S75 and (capacitor sampling)	S76 and (sampl\$3 near2 voltage)	S75 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor))	S74 and @ad<"20040114"	(check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 two\$1way two\$1direction both\$way both\$1direction ((two both) adj (way direction))) near2 current)	S71 and (capacitor sampling) same (sampl\$3 near2 voltage)	S71 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
O _R	OR	O _R	Q _R	O _R	O _R	O _R
ON	O _N	O _N	ON	O _N	Q	OZ
2005/05/16 07:43	2005/05/16 07:03	2005/05/16 07:37	2005/05/16 06:57	2005/05/16 06:56	2005/05/16 07:00	2005/05/16 06:59

13 S78 and (sampl\$3 near2 voltage) US-PGPUB; OR ON 2005/05/16 07:27 USPAT; EPO; JPO; DERWENT; IBM_TDB		
S78 and (sampl\$3 near2 voltage) US-PGPUB; OR ON USPAT; EPO; JPO; DERWENT; IBM_TDB		579
S78 and (sampl\$3 near2 voltage) US-PGPUB; OR ON USPAT; EPO; JPO; DERWENT; IBM_TDB		
JS-PGPUB; OR ON US-PGPUB; OR O		13
OR ON		ge)
OZ	USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB;
		R
2005/05/16 07:27		9
		2005/05